## **Supporting information**

## Cu<sub>3</sub>P/PAN derived N-Doped Carbon Catalyst with Non-toxic Synthesis for Alkaline Hydrogen Evolution Reaction

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Figure S14. SEM images of the Cu foam.



**Figure S15.** (a) HER polarization curves in 1 M KOH solution for Cu<sub>3</sub>P/N-C@Cu foam with different P/PAN loading amount in 1 M KOH solution. (b) XRD pattern for Cu<sub>3</sub>P/N-C@Cu foam.

Sample (P:PAN)	P (mg)	PAN (mg)	NMP (uL)	Doctor blade height (Thickness of coated P/PAN ink) (µm)	*Weight of coated P/PAN (Δw, mg/cm²)	**Calculated Cu3P weight (mg/cm²)
P:PAN (10:0)	100	0	105	18.75	0.2863	2.0456
P:PAN (9:1)	90	10	186	25.00	0.3240	2.0833
P:PAN (8:2)	80	20	210	37.50	0.3616	2.0671
P:PAN (6:4)	60	40	350	50.00	0.4746	2.0348
P:PAN (0:10)	0	100	450	62.50	0.3466	-

Table S1. Precursor composition for synthesis of Cu<sub>3</sub>P, Cu<sub>3</sub>P/N-C and N-C.

\* Weight of coated P and PAN ( $\Delta w$ ) :

(Measured weight of P/PAN coated Cu film) - (Measured weight of Cu film)

\*\*Cu<sub>3</sub>P weight :

(Ratio of P) × ( $\Delta$ w) × (221.5/31)

Ex) P : PAN = 8 : 2  $\rightarrow$  Ratio of P = 0.8,

Molar mass  $\rightarrow$  Cu<sub>3</sub>P = 221.5, P = 31.0

Sample (P:PAN)	Cu (at%)	P (at%)	C (at%)	N (at%)	**Cu <sub>3</sub> P : C (molar ratio)	Notation
P:PAN (10:0)	72.4	27.6	-	-	-	Cu <sub>3</sub> P
P:PAN (9:1)	61.2	21.0	*16.2	*1.6	1:0.8	Cu <sub>3</sub> P/0.8N-C
P:PAN (8:2)	48.8	14.6	31.6	5.0	1 : 1.9	Cu <sub>3</sub> P/1.9N-C
P:PAN (6:4)	19.7	12.5	58.1	9.7	1:8.8	Cu <sub>3</sub> P/8.8N-C
P:PAN (0:10)	-	-	86.7	13.3	-	N-C

Table S2. Material composition of Cu<sub>3</sub>P, Cu<sub>3</sub>P/N-C and N-C obtained by XPS analysis.

\*In the case of P:PAN (9:1), the C-to-N ratio is slightly different, most likely due to the XPS fitting margin caused by the low composition of nitrogen.

 $**Cu_3P : C = (Cu/3, at\%) : (C, at\%)$ 

**Table S3.** Resistance values obtained from the Nyquist plots fitted based on the 2TS circuit model.

Sample	nple $\mathbf{R}_{\mathbf{s}}(\Omega)$		$\mathbf{R}_{1}(\Omega)$	
Cu <sub>3</sub> P	7.566	28.791	9.312	
Cu <sub>3</sub> P/0.8N-C	7.777	26.560	3.918	
Cu <sub>3</sub> P/1.9N-C	7.061	22.911	2.574	
Cu <sub>3</sub> P/8.8N-C	7.019	30.930	4.269	
N-C	11.062	10.267k	8.419k	

\***R**<sub>s</sub>: Uncompensated solution resistance

Table S4.	Comparison	of catalytic	activities	$(Cu_3P)$ .
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\*Graph-derived value

Madaniala	Overpote	ntial of HER in	1 М КОН	Iou	Substrate	
Materials	10 mA/cm <sup>2</sup>	50 mA/cm <sup>2</sup>	100 mA/cm <sup>2</sup>	Journai	Substrate	
Cu <sub>3</sub> P/N-C	211.1 mV	301.8 mV	346.4 mV	This work	Cu foam	
Cu <sub>3</sub> P nanowires	266 mV	*344 mV	382 mV	ACS Sustainable Chem. Eng. 2018, 6, 380	Cu mesh	
Cu <sub>3</sub> P nanoarrays	222 mV (0.1 M KOH)	*364 mV (0.1 M KOH)		ACS Appl. Mater. Interfaces. 2016, 8, 23037	Cu foam	
Cu <sub>3</sub> P nanobush	252 mV	*390 mV		ACS Omega 2016, 1, 1367	Cu mesh	
NiCuP foam		146 mV	*179 mV	Nanoscale 2017, 9, 4401	Stainless steel	
Cu <sub>3</sub> N-Cu <sub>3</sub> P N,P,S doped carbon	68 mV	*130 mV		ChemElectroChem 2020, 7, 289	Ni foam	
Cu <sub>3</sub> P-Co <sub>2</sub> P	*95 mV	*175 mV		Nanoscale 2019, 11, 6394	Ni foam	
Cu <sub>3</sub> P microsheets	130 mV	*200 mV	*255 mV	<i>Adv. Mater. Interfaces</i> 2016, 3, 1600236	Ni foam	
CeO <sub>2</sub> -Cu <sub>3</sub> P		*227 mV	*273 mV	Nanoscale 2018, 10, 2213	Ni foam	
Cu <sub>3</sub> P nanosheets	105 mV	*235 mV		ACS Appl. Mater. Interfaces 2017, 9, 2240	Ni foam	